Supporting Information

Exploring the Surface Sensitivity of ToF-SIMS by Measuring the Implantation Depths and Sampling Depths of Bi_n and C_{60} Ions in Organic Films

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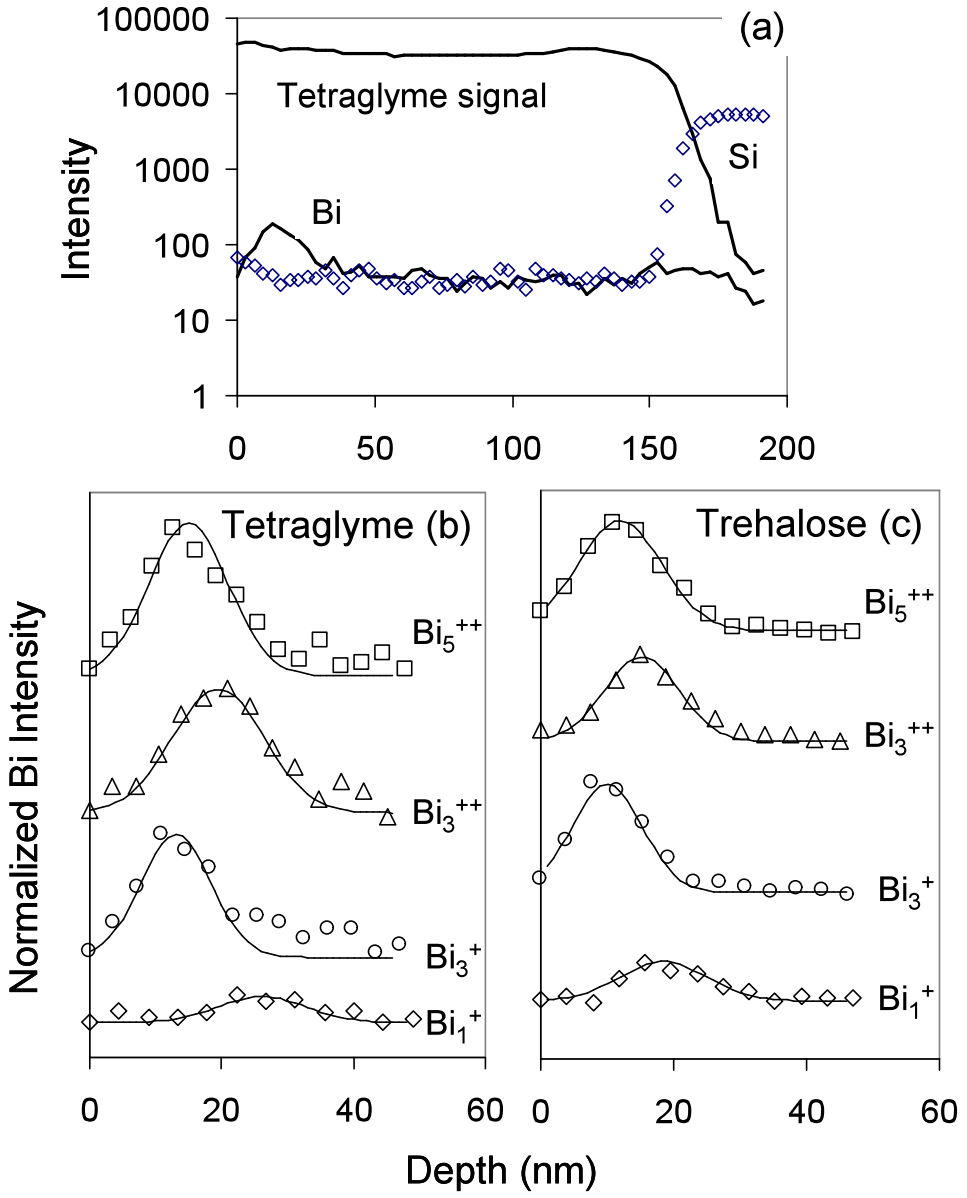

Figure S-1. (a) An example of a C_{60}^{+} single-beam depth profile of an implanted tetraglyme film showing the signal intensities related to the tetraglyme film, implanted bismuth and silicon substrate. Bismuth intensity depth profiles obtained for Bi_1^{+}, Bi_3^{+}, Bi_3^{++}, and Bi_5^{++} implanted (b) tetraglyme and (c) trehalose films. A guassian peak has been fit to each bismuth profile. The bismuth signals (offset) are normalized to the number of incident C_{60} ions.

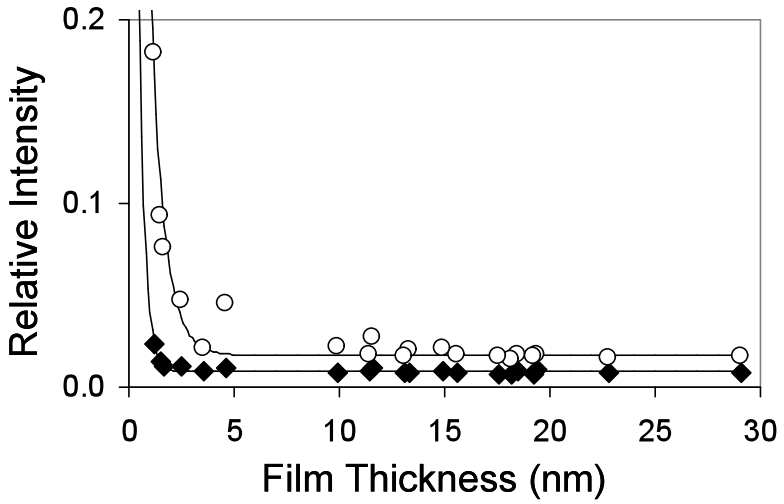

Figure S-2. The relative intensity of the secondary ion $C_4H_8N^+$ at *m/z* 70 versus tetraglyme overlayer thickness for Bi_1^+ (◆) and Bi_3^+ (O) primary ions. The data points obtained using Bi_3^{++}, Bi_5^{++}, and C_{60}^{++} primary ions were not included for ease of viewing.